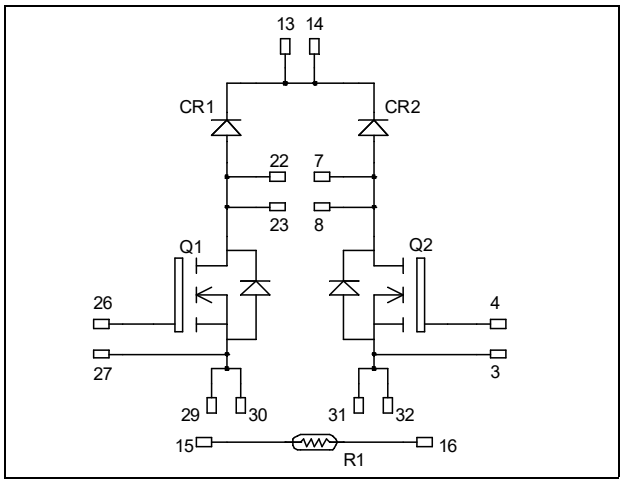
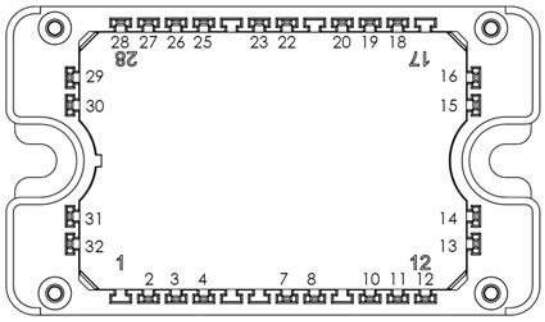
APTC60DDAM35T3G

Dual boost chopper
Super Junction MOSFET
Power Module

V_{DSS} = 600V
R_{DSon} = 35mΩ max @ Tj = 25°C
I_D = 72A @ Tc = 25°C





All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 …

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- **Super junction MOSFET**
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single boost of twice the current capability
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings (per super junction MOSFET)

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Voltage		600	V
I_D	Continuous Drain Current	T_c = 25°C	72	A
		T_c = 80°C	54	
I_{DM}	Pulsed Drain current		288	
V_{GS}	Gate - Source Voltage		±20	V
R_{DSon}	Drain - Source ON Resistance		35	mΩ
P_D	Power Dissipation	T_c = 25°C	416	W
I_{AR}	Avalanche current (repetitive and non repetitive)		20	A
E_{AR}	Repetitive Avalanche Energy		1	mJ
E_{AS}	Single Pulse Avalanche Energy		1800	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (per super junction MOSFET)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V,V_{DS} = 600V			40	µA
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 72A			35	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 5.4mA	2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V			±150	nA

Dynamic Characteristics (per super junction MOSFET)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		14		nF
C_{oss}	Output Capacitance			5.13		
C_{rss}	Reverse Transfer Capacitance			0.42		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 300V I_D = 72A		518		nC
Q_{gs}	Gate – Source Charge			58		
Q_{gd}	Gate – Drain Charge			222		
$T_{d(on)}$	Turn-on Delay Time	**Inductive Switching @ 125°C** V_{GS} = 15V V_{Bus} = 400V I_D = 72A R_G = 2.5Ω		21		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			283		
T_f	Fall Time			84		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 400V I_D = 72A, R_G = 2.5Ω		1340		µJ
E_{off}	Turn-off Switching Energy			1960		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 400V I_D = 72A, R_G = 2.5Ω		2192		µJ
E_{off}	Turn-off Switching Energy			2412		
R_{thJC}	Junction to Case Thermal Resistance				0.3	°C/W

Chopper diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					600	V
I_{RM}	Reverse Leakage Current	V_R=600V				350	µA
I_F	DC Forward Current		Tc = 80°C		80		A
V_F	Diode Forward Voltage	I_F = 80A V_{GE} = 0V	T_j = 25°C		1.45		V
			T_j = 125°C		1.35		
t_{rr}	Reverse Recovery Time	I_F = 80A V_R = 300V di/dt =4500A/µs	T_j = 25°C		95		ns
			T_j = 125°C		115		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		5.2		µC
			T_j = 125°C		8		
R_{thJC}	Junction to Case Thermal Resistance					0.8	°C/W

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_J	Operating junction temperature range			-40	150	°C
T_{JOP}	Recommended junction temperature under switching conditions			-40	$T_J$max -25	
T_{STG}	Storage Temperature Range			-40	125	
T_C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

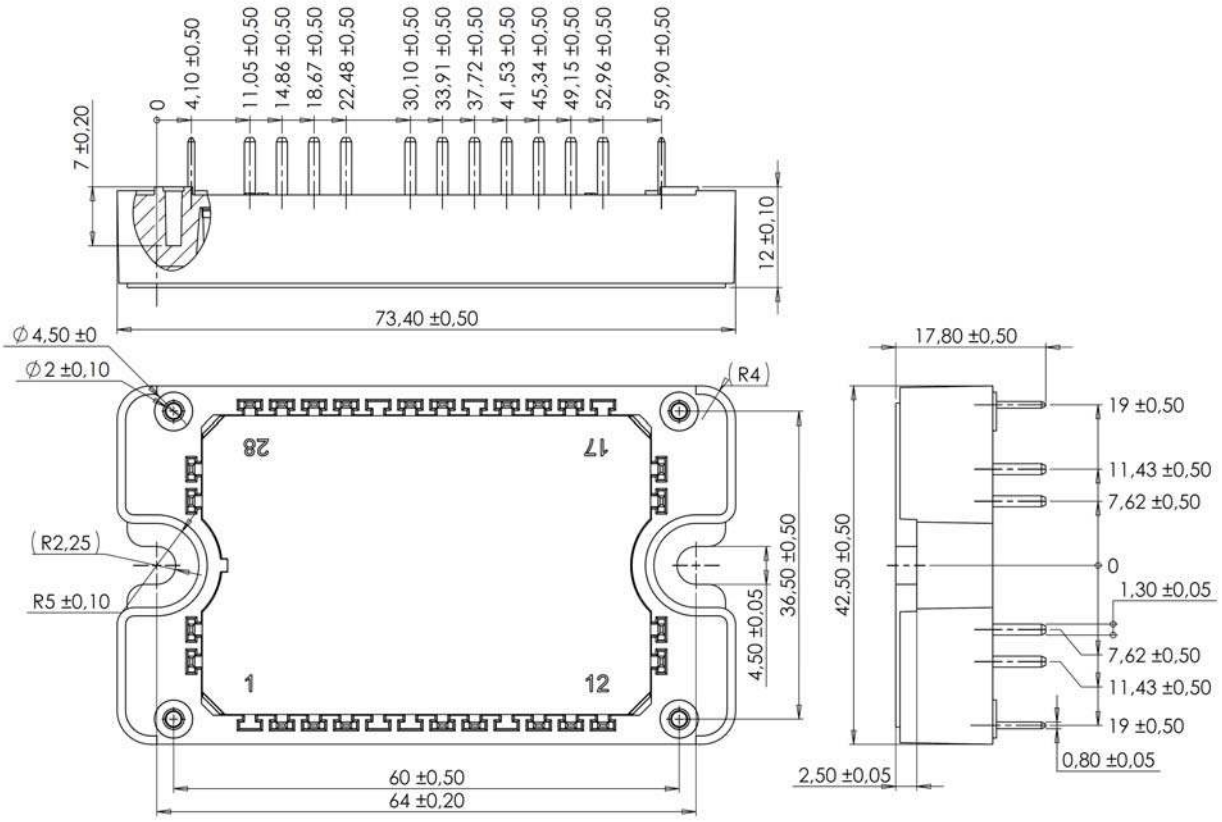
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
$\Delta B/B$		T_C=100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

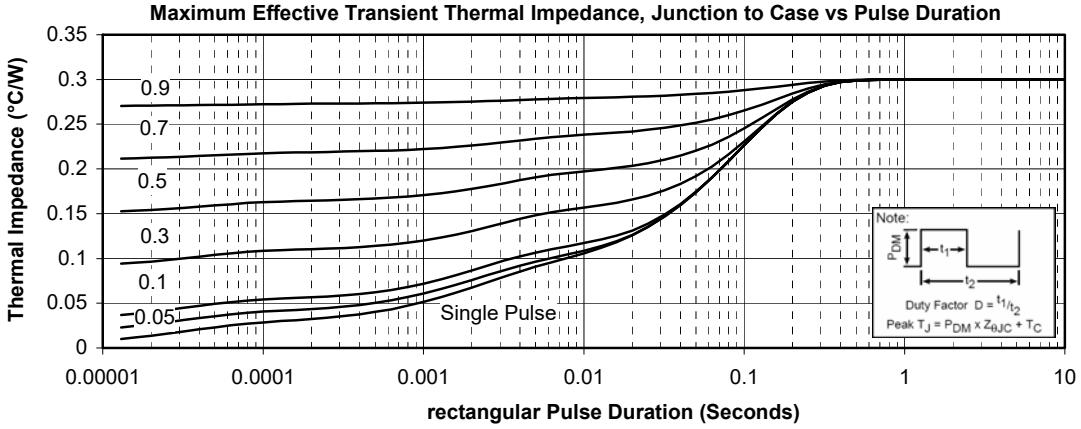
T: Thermistor temperature
R_T: Thermistor value at T

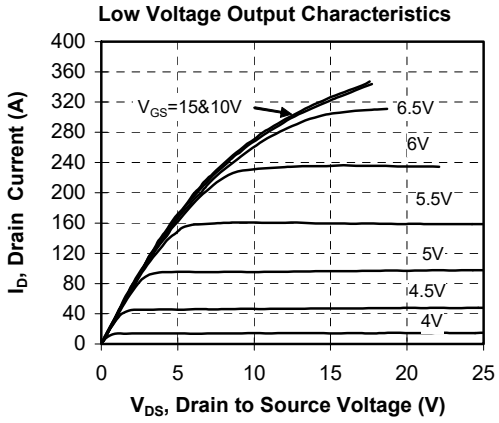
Package outline (dimensions in mm)

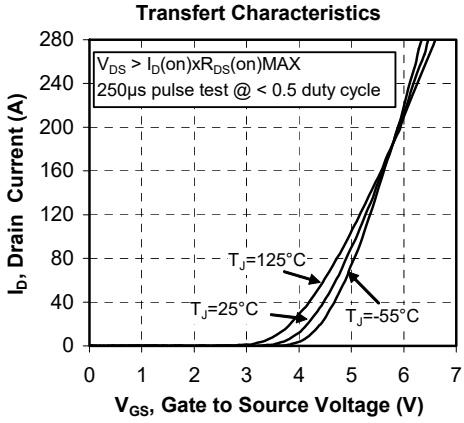


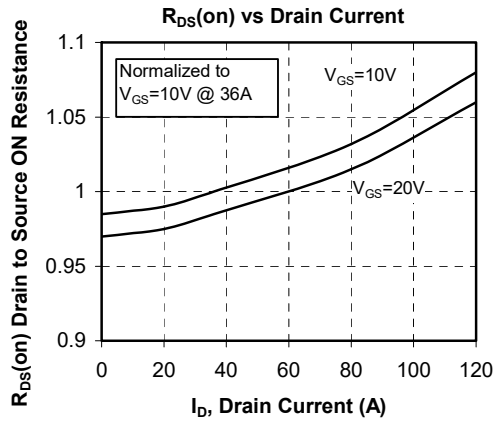
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

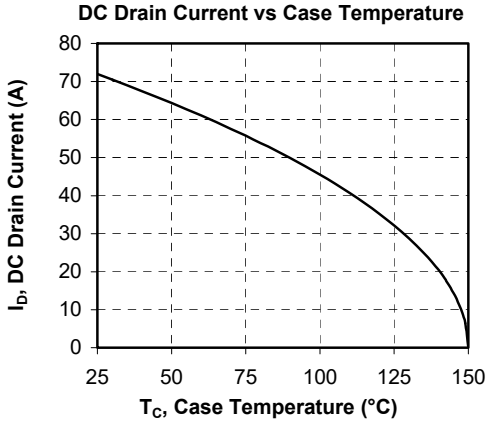
Typical Super junction MOSFET Performance Curve



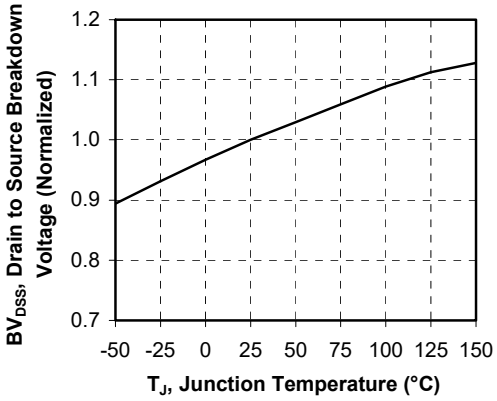




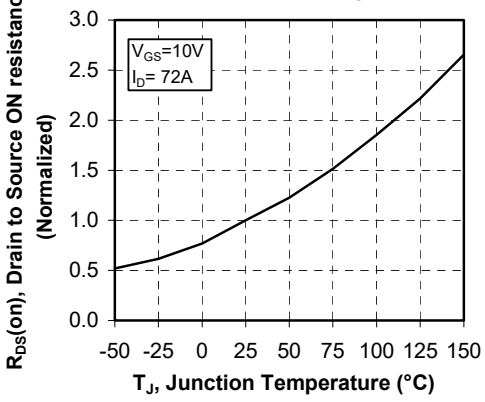




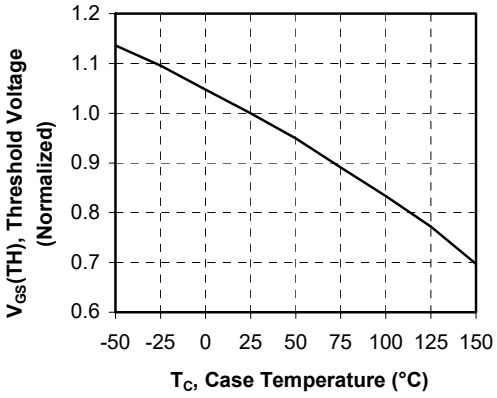
Breakdown Voltage vs Temperature



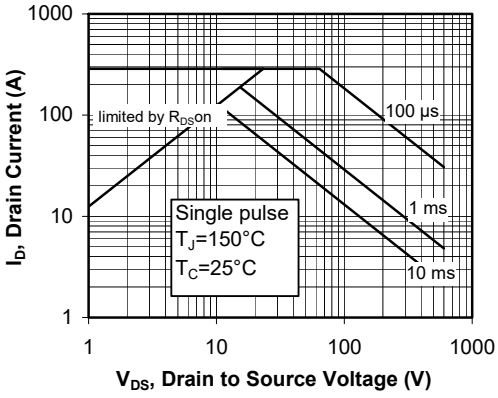
ON resistance vs Temperature



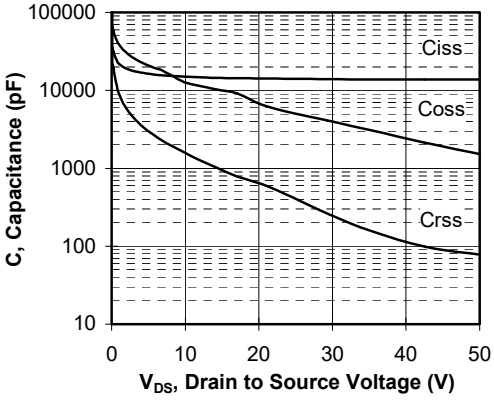
Threshold Voltage vs Temperature



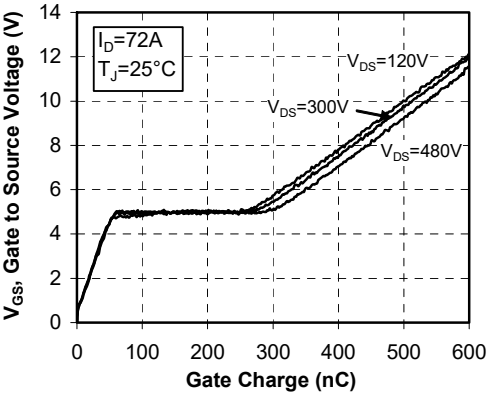
Maximum Safe Operating Area



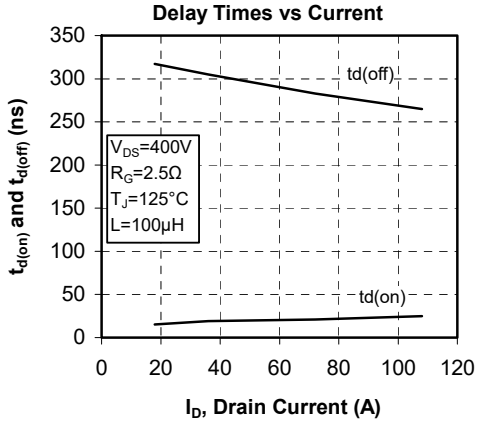
Capacitance vs Drain to Source Voltage



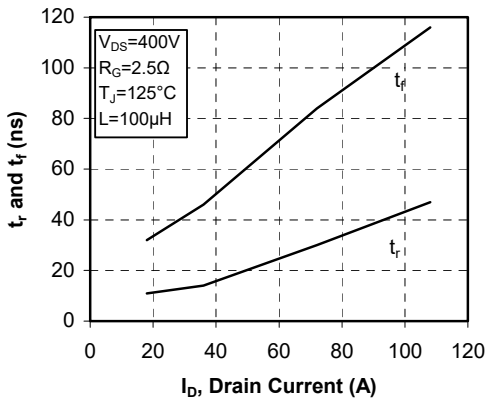
Gate Charge vs Gate to Source Voltage



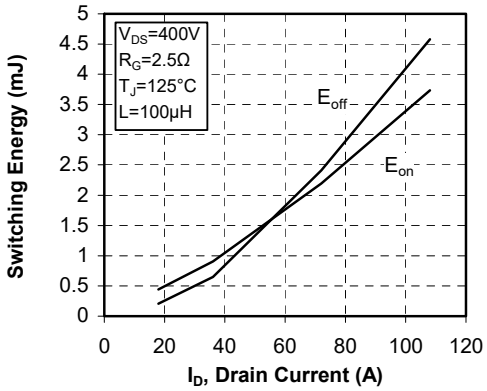
Delay Times vs Current



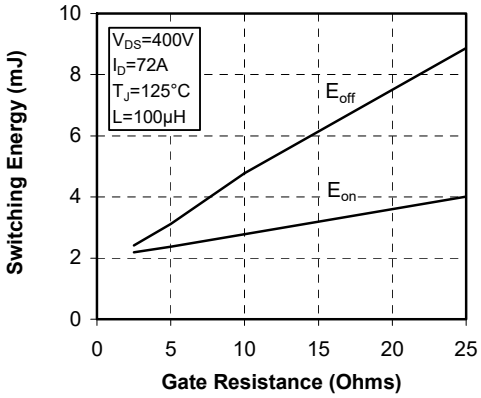
Rise and Fall times vs Current



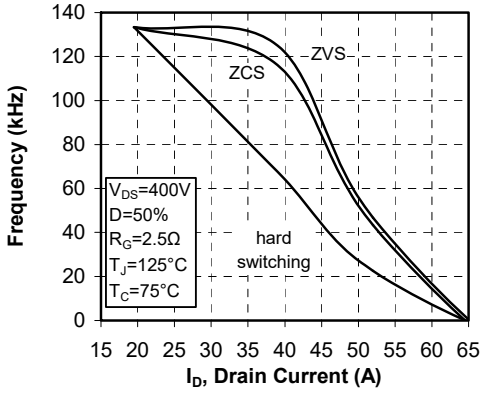
Switching Energy vs Current



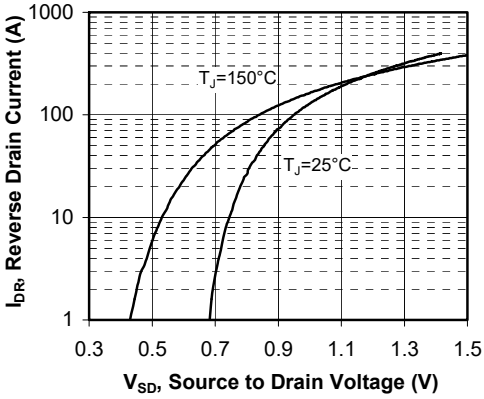
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



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